

R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



| R-C VALUES FOR TANK CONFIGURATION | | | |
|--|---------|------------|------|
| Thermal Resistance (°C/W) | | | |
| Junction to | Ambient | Case | Foot |
| RT1 | N/A | 85.0649 m | N/A |
| RT2 | N/A | 389.7232 m | N/A |
| RT3 | N/A | 257.7333 m | N/A |
| RT4 | N/A | 367.4785 m | N/A |
| Thermal Capacitance (Joules/°C) | | | |
| Junction to | Ambient | Case | Foot |
| CT1 | N/A | 866.2762 m | N/A |
| CT2 | N/A | 1.9029 m | N/A |
| CT3 | N/A | 35.7097 m | N/A |
| CT4 | N/A | 89.8563 m | N/A |

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.



R-C THERMAL MODEL FOR FILTER CONFIGURATION



| R-C VALUES FOR FILTER CONFIGURATION | | | |
|--|---------|------------|------|
| Thermal Resistance (°C/W) | | | |
| Junction to | Ambient | Case | Foot |
| RF1 | N/A | 321.9701 m | N/A |
| RF2 | N/A | 139.7272 m | N/A |
| RF3 | N/A | 439.1969 m | N/A |
| RF4 | N/A | 197.3941 m | N/A |
| Thermal Capacitance (Joules/°C) | | | |
| Junction to | Ambient | Case | Foot |
| CF1 | N/A | 1.7350 m | N/A |
| CF2 | N/A | 1.1826 m | N/A |
| CF3 | N/A | 26.8611 m | N/A |
| CF4 | N/A | 173.6240 m | N/A |

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

